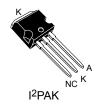




### Automotive 650 V power Schottky silicon carbide diode





#### **Features**



- · No reverse recovery charge in application current range
- · Switching behavior independent of temperature
- Recommended to PFC applications
- · PPAP capable
- ECOPACK<sup>®</sup>2 compliant component

#### **Description**

The SiC diode is an ultra-high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, the STPSC10C065-Y will boost performance in hard switching conditions.

Product status link	
STPSC10C065-Y	

Product summary		
I <sub>F(AV)</sub>	10 A	
$V_{RRM}$	650 V	
T <sub>j</sub> (max.)	175 °C	



### 1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Paran	Parameter		
$V_{RRM}$	Repetitive peak reverse voltage T <sub>j</sub> from -40 °C to 175 °C		650	V
I <sub>F(RMS)</sub>	Forward rms current		22	Α
I <sub>F(AV)</sub>	Average forward current T <sub>c</sub> = 120 °C, DC current <sup>(1)</sup>			Α
		$t_p$ = 10 ms sinusoidal, $T_c$ = 25 °C	85	
$I_{FSM}$	Surge non repetitive forward current	$t_p$ = 10 ms sinusoidal, $T_c$ = 125 °C	75	Α
		t <sub>p</sub> = 10 μs square, T <sub>C</sub> = 25 °C	500	
T <sub>stg</sub>	Storage temperature range	-55 to +175	°C	
Tj	Operating junction temperature <sup>(2)</sup>	-40 to +175	°C	

<sup>1.</sup> Value based on  $R_{th(j-c)}$  max.

**Table 2. Thermal resistance parameters** 

Symbol	Parameter	Va	Unit	
Syllibol	r al allietei	Тур.	Max.	Offic
R <sub>th(j-c)</sub>	Junction to case	1.3	2.0	°C/W

Table 3. Static electrical characteristics

	Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Deverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	9	100	μA	
	I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 150 °C		-	85	425		
	V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A	-	1.56	1.75	V
			T <sub>j</sub> = 150 °C		-	1.98	2.50	

<sup>1.</sup> Pulse test:  $t_p = 10$  ms,  $\delta < 2\%$ 

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.12 \times I_{F}^{2}_{(RMS)}$$

**Table 4. Dynamic electrical characteristics** 

Symbol	Parameter	Test conditions	Тур.	Unit
Q <sub>Cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 400 V	26.4	nC
C <sub>j</sub> Total capacitance		V <sub>R</sub> = 0 V, T <sub>c</sub> = 25 °C, F = 1 MHz	480	pF
	V <sub>R</sub> = 300 V, T <sub>c</sub> = 25 °C, F = 1 MHz	47	pΓ	

1. Most accurate value for the capacitive charge:  $Q_{Cj}(V_R) = \int\limits_0^V C_j(V) dV$ 

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<sup>2.</sup>  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

<sup>2.</sup> Pulse test:  $t_p = 500 \ \mu s, \ \delta < 2\%$ 

### 1.1 Characteristics (curves)

current (typical values, low level)  $I_F(A)$ Pulse test : t<sub>n</sub> = 500 µs 16 T<sub>a</sub> = 100 °C 12 T<sub>o</sub> = 150 °C T<sub>a</sub> = 175 °C 8 . T<sub>a</sub> = 25 °C  $V_F(V)$ -40 °C 0.0 0.5 1.0 1.5 2.0 2.5 3.0

Figure 1. Forward voltage drop versus forward

Figure 2. Forward voltage drop versus forward current (typical values, high level)  $I_F(A)$ 100 Pulse test : t<sub>n</sub> = 500 µs 80 60 40 T<sub>a</sub> = 150 °C 20  $V_F(V)$ 0 5 7 0 1 3

I<sub>R</sub>(μA)

1.E+02

1.E+01

1.E-01

1.E-02

1.E-03

1.E-04

0 50 100 150 200 250 300 350 400 450 500 550 600 650

Figure 3. Reverse leakage current versus reverse

voltage applied (typical values)

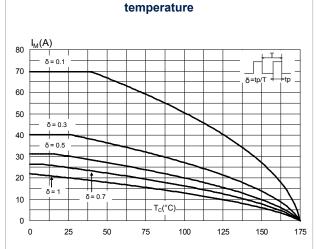


Figure 4. Peak forward current versus case

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Figure 5. Junction capacitance versus reverse voltage applied (typical values)

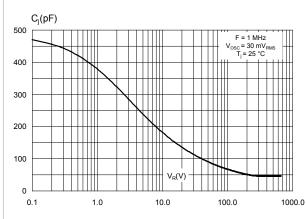


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

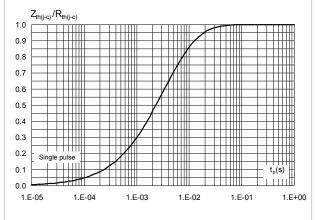


Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

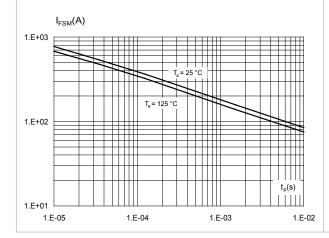
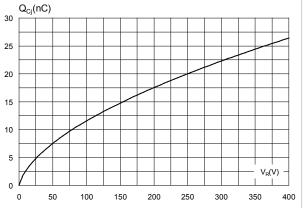


Figure 8. Total capacitive charges versus reverse voltage applied (typical values)



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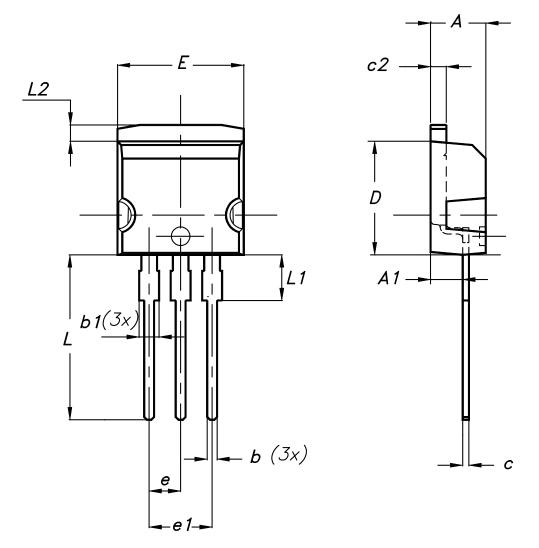
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

### 2.1 I<sup>2</sup>PAK package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)

Figure 9. I<sup>2</sup>PAK package outline



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Table 5. I<sup>2</sup>PAK package mechanical data

	Dimensions				
Ref.	Millin	neters	Inches (for reference only)		
	Min.	Max.	Min.	Max.	
A	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
Е	10.00	10.40	0.394	0.409	
L	13.00	14.00	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

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# 3 Ordering information

**Table 6. Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10C065RY	PSC10C065RY	I²PAK	1.5 g	50	Tube

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## **Revision history**

**Table 7. Document revision history** 

Date	Revision	Changes
16-Feb-2018	1	First issue.
24-Sep-2018	2	Corrected cover image.

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